/Improved Optoelectronic Characteristics of Post-Annealed Ti/Al/ITO Transparent Conducting Electrodes Deposited on n-GaN

Ahmad Hadi Ali^{1,2}, Ahmad Shuhaimi³, Zainuriah Hassan²

 Science Department, Faculty of Science, Technology and Human Development, Universiti Tun Hussein Onn Malaysia, Johor, Malaysia.
Institute of Nano Optoelectronic Research and Technology (INOR), School of Physics, Universiti Sains Malaysia, Penang, Malaysia, Paculty of Science, Universiti Malaya, Kuala Lumpur, Malaysia.

We report on the improved structural, electrical and optical properties of the Ti/Al/ITO transparent conducting electrodes (TCEs) deposited on n-GaN. The TCEs were deposited by RF/DC magnetron sputtering under Ar ambient at room temperature. The as-deposited TCEs were annealed at 600 °C in N₂ ambient for 15 min. The structural, electrical and optical properties of the TCEs were characterized by 2-Theta X-ray diffraction (XRD), atomic force microscope (AFM), Hall effects, I-V and UV-visible measurement system. From XRD measurement, significant ITO (222) and (411) peaks were observed after the sample was post-annealed at 600 °C. Morphological analysis by AFM shows that surface roughness R_q of the post-annealed sample is smoother as compared to the as-deposited sample. The electrical resistivity of the TCEs layer decreases to $8.607 \times 10^{-5} \Omega$ -cm after the post-annealing process. Further analysis on the I-V characteristics reveals that the post-annealed samples have better Ohmicbehavior than the as-deposited sample. The post-annealed sample shows high optical transmittance characteristics in visible spectrum of ~95%. The figure of merit (FOM) of the as deposited and post-annealed samples are $2.39 \times 10^{-4} \Omega^{-1}$ and $5.91 \times 10^{-2} \Omega^{-1}$, respectively. Therefore, the post-annealed TCEs show the best electrical and optical quality due to the improved structural and morphological characteristics.